

Abstracts

A 2-6.2 GHz, 300 mW GaAs MESFET Amplifier

D.P. Hornbuckle. "A 2-6.2 GHz, 300 mW GaAs MESFET Amplifier." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 288-290.

The development of a 2-6.2 GHz GaAs MESFET amplifier with 300 mW minimum power in production, and 600 mW minimum power with high breakdown-voltage MESFETs, is described.

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